

# Rapid Thermal Process Oven with Vacuum up to 150 mm dia. or 156 mm x 156 mm substrate size



- For wafer size up to 150 mm dia.
- Ramp up rate up to 75 K/sec
- Control **SIMATIC**® with 7" touch panel
- Vacuum up to 10<sup>-3</sup> hPa
- Process gas line with MFC for N<sub>2</sub>

Technical and design changes reserved

# FEATURE

- Precise fast ramp up and fast ramp down rates
- Excellent temperature uniformity
- Up to 4 gas lines (MFC)
- Integrated data logging
- Heated by Infrared Lamps
- 50 programs with 50 steps each
- Small foot print

## APPLICATION

- Implantation/Contact Annealing
- RTP, RTA, RTO, RTN
- Operation with inert gases, Oxygen, Hydrogen, Forming gas
- SiAu, SiAl, SiMo Alloying
- Low k dielectrica

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- · Crystallization & densification
- Si-Solar Wafer Cells on glass by Si-Wafer bonding



- Rapid Thermal Annealing Process Oven with vacuum
- Touch Panel Svivel
- Programmable temperature profiles
- Record of process data
- Process in different gas atmospheres



The **RTP-150** Rapid Thermal Annealing Vacuum oven is an excellent tool for various semiconductor up to 150 mm diameter wafer or 156 mm x 156 mm substrate size.

Some examples for applications: Laboratory furnace for all kind of developers implementing and researching new processes, prototype research, environmental research purposes and for small preseries or series.

#### **PROCESS GASES**

The RTP-150 can be used with standard process gases, like Nitrogen, Oxygen, Forming Gas. The chamber is sealed and can easily be cleaned.

#### **FLOW METER**

One gas line with Mass Flow Controller (MFC) for Nitrogen (5 nlm = norm liter per minute) is default, three more gas lines (Option: MFC) are possible.

#### **VACUUM**

The system is vacuum capable of up to 10<sup>-3</sup> hPa. For higher vacuum we offer the model **RTP-150-HV** (see separate data sheet)

#### **HEATING**

The maximal achievable temperature is 1000 °C. Key features are precisely controlled fast ramp-up 75 K/sec) and excellent ramp-down rates (depends on temperature and loading).

#### **TEMPERATURE**

The RTP-150 allows an excellent temperature distribution and homogenity. Optionally a graphite suzceptor can be inserted into the quartz chamber (Option: GP Graphite Plate or Suszeptor).

#### **PROGRAMMING**

The RTP-150 is equipped with a 7" touch panel which allows easy and comfortable programming directly on the unit.50 programs with 50 steps each can be stored. Unlimited programs can be up- and downloaded from external storage medium.



#### PROCESS CONTROL

The software allows the permanent monitoring, read- out and analysis of >temperature >process gas flow >cooling water level status

>pressure value and status

#### COOLING

The cooling of the parts in the quartz chamber is realized by Nitrogen gas which will be led through the chamber. For chamber cooling we recommend a closed loop water cooling system.

(Accessories: WC-III or WC-IV)

#### **OTHERS**

An interlock function as well as an Emergency-OFF-Button (EMO) are default.

#### SPECIAL

This oven can also be orderd as "double chamber oven". By adding a second process chamber (Option: PC-150) the oven does have 2 process chambers and one controller unit. This saves money when 2 different processes are needed and the chambers shall not be cleaned due to contamination or other reasons.

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# SPECIFICATION

Max. part size

Chamber material

Part holder

Chamber height

Vacuum capability

Process chamber size

Temperature max.

Temp. unifomity

Heating

Ramp up rate

Ramp down rate

Flow Controller

Controller

Chamber cooling

**Substrate Cooling** 

150 mm dia. or 156 mm x 156 mm

Quartz glass chamber

Quartz universal holder for either 156 x 156 mm solar wafer

or 150 mm wafer dia.

40 mm

Up to 10<sup>-3</sup> hPa

325 mm x 214 mm x 40 mm (W x D x H)

1000 °C (higher on request)

≤ 1,5% of set temperature

Top and bottom heating with 24 IR Lamps (21 kW)

Up to 75 K/sec

T = 1000°C > 400°C: 200 K/min, T = 400°C > 100°C: 30 K/min

Mass Flow Controller (Nitrogen 5 nlm = norm liter per minute)

SIMACTIC® 50 programs with 50 steps each

Water cooled

By Nitrogen Gas

# TECHNICAL DATA

Dimension oven

Weight

Electrical connection

503 mm x 525 mm x 570 mm (W x D x H)

55 kg

400/230V, 21 kW



## OPTIONS

RTP-H2 RTP-H2S	Hydrogen option with Safety device (Sensor and Hydrogen monitoring) Safety device for Hydrogen option (with cover and sensor)
RTP-MFC	Additional process gas line with Mass Flow Controller (max. 3 add) *
	* = all in all max. 4 process gas lines
RTP-Ox	Oxygen Analyser to measure Oxygen residues
	(not in combination with Hydrogen Option)
RTP-MM	Moisture Analyzer to measure moisture residues in the chamber
RTP-SW	Switchbox for chiller and vacuum pump
RTP-TC	add. Thermocouple to measure on device (plugged in chamber, max. 1)
VAC I	Basic Vacuum up to 3 hPa, Vacuum sensor, vacuum valve excl. pump
VAC II	Comfort Vacuum up to 10 <sup>-3</sup> hPa, Pirani Sensor, vacuum valve, excl.pump
VCR	Tubing made of VCR (welded)
RTP-CAB	Oven integrated as floor model into a cabinet with Uni. Heat Exchanger

# ACCESSORIES

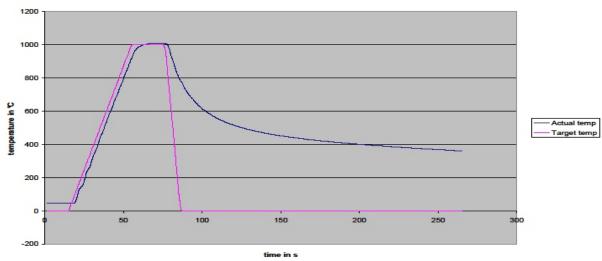
RTP-GP-150 Graphite Plate or susceptor (optional SiC coated)

RTP-PC-150 add. 100 mm oven chamber ("double chamber( for usage of 2 chambers)

RTP-QR-75 Adapter (quartz ring) for 75 mm wafer RTP-QR-100 Adapter (quartz ring) for 100 mm wafer

MP Membrane/diaphragm pump for vacuum up to 3 hPa RVP Rotary vane pump or dry pump for vacuum up to 10<sup>-3</sup> hPa

#### Anneal 1000℃ 15 s



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